

FORM HDP-1449 (Based on Form PTO-1449)

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Sheet 1 of 1

ATTORNEY DOCKET NO.	SERIAL NO.
5077-000073/COA	10/625256
APPLICANT	
Toshiya Yokogawa et al.	
FILING DATE	GROUP
July 23, 2003	

U.S. PATENT DOCUMENTS

Ref. Desig.	Examiner's Initials	Document Number	Date	Name	Class/ Subclass	(If appropriate) Filing Date
1.	PC	5,493,136	02/20/1996	Matsuzaki et al.	257/287	

FOREIGN PATENT DOCUMENTS

Ref. Desig.	Examiner's Initials	Document Number	Date	Country	Class/ Subclass	Translation Yes	No
1.	PC	06310536 A	11/04/1994	Japan		*	

OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, etc.)

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1.	PC	Preliminary Manuscript of the 45 th Lecture Presentation by Japan Society of the Applied Physics, Volume No. 1, page 422, 30p-YG-4, March 28, 1998.
2.	PC	Notice of Reasons of Rejection for Japanese Patent App. No. 2001-566193 mailed September 16, 2003, and English translation.

* Japanese Patent App. No. 06310536 A corresponds to U.S. Patent No. 5,493,136.

Examiner: PHAT X. CAO

Date Considered: 5/12/05

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Herewith	2814

U.S. PATENT DOCUMENTS

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1.	PC	3,739,243	6/12/1973	Semichon, et al.	257/484	
2.	PC	4,882,609	11/21/1989	Schubert, et al.	257/194	
3.	PC	6,388,272	5/14/2002	Odekirk	257/77	
4.	PC	5,488,237	1/30/1996	Kuwata [New art]	257/194	

FOREIGN PATENT DOCUMENTS

Ref. Desig.	Examiner's Initials	Document Number	Date	Country	Class/ Subclass	Translation Yes No
1.	PC	WO 01/67521 A1	9/13/2001	WIPO		Abstract
2.	PC	WO 01/93339 A1	12/6/2001	WIPO		Abstract
3.	PC	EP 0612104 A2	8/24/1994	Europe		Abstract
4.	PC	JP 54-132173	10/13/1979	Japan		Abstract
5.	PC	JP 5-13446	1/22/1993	Japan		Abstract
6.	PC	JP 6-349860	12/22/1994	Japan		Abstract
7.	PC	JP 9-289216	11/4/1997	Japan		Abstract
8.	PC	EP 0555886 A2	8/18/1993	Europe [New art]		

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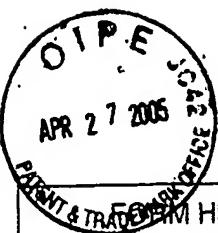
Ref. Design.	Examiner's Initials	Other Documents
2.	pc	A. Konstantinov, et al., "Investigation of lo-hi-lo and delta-doped silicon carbide structures", Mat. Res. Soc. Symp. Proc. Vol. 640, 2001, pp. H2.4.1-6.
3.	pc	Shui Jinn Wang, et al., "Schottky/Two-Dimensional Hole Gas Silicon Barrier Diodes with Single and Coupled Delta-Doped Wells", Jpn. J. Appl. Phys. Vol. 33, No. 4B, Part 1, 1 April 1994, pp. 2429-2434.
4.	pc	W.C. Hsu, et al., "A Quantum Well- doped GaAs Fet Fabricated by Low-Pressue Metal Organic Chemical Vapro Deposition", Solid-State Electronics, Vol. 34, No. 6, 1 June 1991, pp. 649-653.
5.	pc	S.M. Bedair, "Selective-area and sidewall growth by atomic layer epitaxy", Semiconductor Science and Technology, Vol. 8, No. 6, 1 June 1993, pp. 1052-1062.
6.	pc	European Patent Publication No. EP 0 309 290 A1
7.	pc	"Characterization of Double Pulse-Doped Channel GaAs MESFET's", Shigeru Nakajima, et al., IEEE Electron Device Letters, Vol. 14, No. 3, March 1993, pp. 146-148.
8.	pc	"Stark Effect Studied in -doped GaAs Structures", A. Ben Jazia, et al., Semicond. Sci. Technol. 12 (1997), pp. 1388-1395.
9.	pc	"Vertical Hot-Wall Type CVD for SiC Growth", Kunimasa Takahashi, et al., Materials Science Forum Vols. 338-342 (2000), pp. 141-144.
10.	pc	"Electronic Properties of Nitrogen Delta-Doped Silicon Carbide Layers", Toshiya Yokogawa, et al., Mat. Res. Soc. Symp. Proc. Vol. 640 (2001), pp. H2.5.1-H2-5-6.
11.	pc	Partial Supplementary European Search Report EP 00 97 6350, 12/20/2002.

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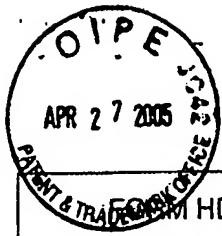
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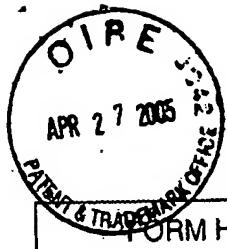
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